Distributed Gate Thyristor
Type SA22ZP1605EG

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Date: September, 2020
Data Sheet Issue: 1

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SA	22	ZP	1605	E	G	
-	Voltage Code	Outline Code	Current code	Type code	t_q code	Optional code
t_q code: E = 25µs, F = 30µs, G = 35µs, H = 40µs, J = 50µs						

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Absolute Maximum Ratings

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V_{DRM}	Repetitive peak off-state voltage, (note 1)	2200	V
V_{DSM}	Non-repetitive peak off-state voltage, (note 1)	2200	V
V_{DDC}	Maximum DC of-state voltage, (note 1)	1450	V
V_{RRM}	Repetitive peak reverse voltage, (note 1)	2200	V
V_{RSM}	Non-repetitive peak reverse voltage, (note 1)	2200	V
V_{RDC}	Maximum DC revrese voltage, (note 1)	1450	V
note 1)	De-rating factor of 0.13%/°C is applicable for T_j below 25°C		

	OTHER RATINGS	MAXIMUM LIMITS	UNITS
$I_{T(AV)M}$	Maximum average on-state current, T_{sink} = 55°C, (note 1)	1605	A
$I_{T(AV)M}$	Maximum average on-state current, T_{sink} = 85°C, (note 1)	1020	A
$I_{T(AV)M}$	Maximum average on-state current, T_{sink} = 85°C, (note 2)	510	A
$I_{T(RMS)}$	Nominal RMS on-state current, T_{sink} = 25°C (note 1)	3315	A
$I_{T(d.c.)}$	D.C. on-state current, T_{sink} = 25°C, (note 3)	2545	A
I_{TSM}	Peak non-repetitive surge current t_p = 10ms, V_{RM} = 60%V_{RRM}, (note4)	20.7	kA
I_{TSM2}	Peak non-repetitive surge current t_p = 10ms, $V_{RM} \leq$ 10V, (note 4)	23.0	kA
I^2t	I^2t capacity for fusing t_p = 10ms, V_{RM} = 60%V_{RRM}, (note 4)	$2.14 \cdot 10^6$	A^2s
I^2t	I^2t capacity for fusing t_p = 10ms, $V_{RM} \leq$ 10V, (note 4)	$2.65 \cdot 10^6$	A^2s
$(di/dt)_{cr}$	Critical rate of rise of on-state current (repetitive), (note 5)	1000	A/µs
	Critical rate of rise of on-state current (non repetitive), (note 5)	500	A/µs
V_{RGM}	Peak reverse gate voltage	5	V
$P_{G(AV)}$	Mean forward gate power	5	W
P_{GM}	Peak forward gate power	30	W
T_{jop}	Operating temperature range	-40 to +125	°C
T_{stg}	Storage temperature range	-40 to +150	°C
note 1)	Double-side cooled, single phase, 50Hz, 180° half-sinewave.		
note 2)	Single-side cooled, single phase, 50Hz, 180° half-sinewave.		
note 3)	Double-side cooled		
note 4)	Half-sinewave, 125°C T_j initial		
note 5)	V_D = 67%V_{DRM}, I_{FG} = 2A, $t_R \leq$ 0.5µs, T_{case} = 125°C		

Characteristics

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNITS
V_{TM}	Maximum peak on-state voltage	I_{TM} = 1700A	-	-	2.45	V
		I_{TM} = 5100A	-	-	3.07	V
V_{T0}	Threshold voltage		-	-	2.11	V
r_T	Slope resistance		-	-	0.20	mΩ
$(dv/dt)_{CR}$	Critical rate of rise of off-state voltage	V_D = 80%V_{DRM}, Linear ramp, Gate o/c	200	-	-	V/µs
I_{DRM}	Peak off-state current	Rated V_{DRM}	-	-	100	mA
I_{RRM}	Peak reverse current	Rated V_{RRM}	-	-	100	mA
V_{GT}	Gate trigger voltage	T_j = 25°C, V_D = 10V, I_T = 3A	-	-	3.0	V
I_{GT}	Gate trigger current		-	-	300	mA
V_{GD}	Gate non-trigger voltage	Rated V_{DRM}	-	-	0.25	V
I_H	Holding current	T_j = 25°C	-	-	1000	mA
t_{GD}	Gate controlled turn-on delay time	V_D = 67%V_{DRM}, I_{TM} = 1000A, di/dt = 60A/µs, I_{FG} = 2A, t_r = 0.5µs, T_j = 25°C	-	0.4	1.0	µs
t_{GT}	Turn-on time		-	1.0	2.0	µs
Q_{RR}	Recovered charge	I_{TM} = 1000A, t_p = 1000µs,di/dt = 60A/µs, V_R = 50V	-	900	1000	µC
Q_{RA}	Recovered charge, 50% Chord		-	540	-	µC
I_{RM}	Reverse recovery current		-	200	-	A
t_{RR}	Reverse recovery time		-	5.4	-	µs
t_{GQ}	Turn-off time (note 2)	I_{TM} = 1000A, t_p = 1000µs, di/dt = 60A/µs, V_R = 50V, V_{DR} = 33%V_{DRM}, dV_{DR}/dt = 20V/µs	-	30	-	µs
		I_{TM} = 1000A, t_p = 1000µs, di/dt = 60A/µs, V_R = 50V, V_{DR} = 33%V_{DRM}, dV_{DR}/dt = 200V/µs	-	40	-	µs
R_{thJK}	Thermal resistance, junction to sink (note 3)	Double-side cooled	-	-	0.015	K/kW
		Anode-side cooled	-	-	0.028	K/kW
		Cathode-side cooled	-	-	0.033	K/kW
F	Mounting force	(note 3)	27	-	34	kN
W_t	Weight		-	550	-	g

note 1) Unless otherwise indicated T_j = 125°C

note 2) The required t_Q (specified with dV_{DR}/dt = 200V/µs) is 35µs

note 3) For other clamp forces, please consult factory

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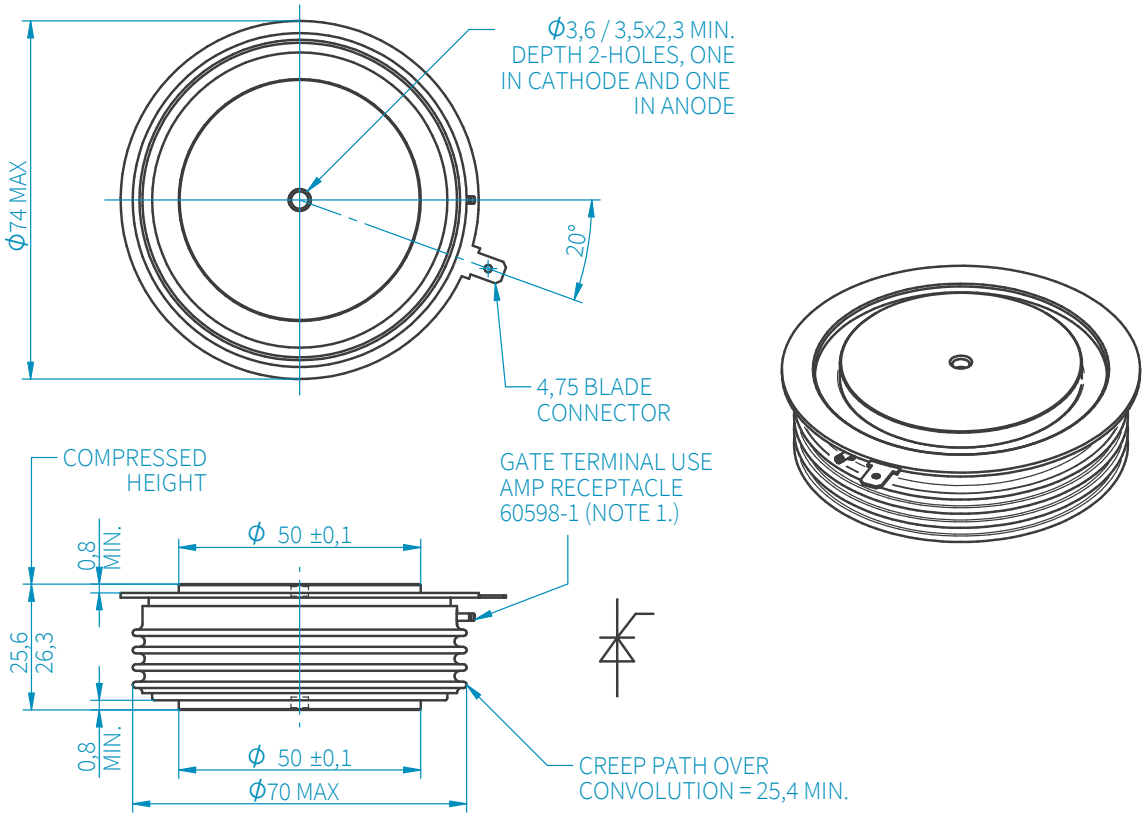
Outline Drawing



SANCONA®
technical solutions

SANCONA GmbH
An der Hebemärchte 26
D-04316 Leipzig

// +49 341 652355-0
+49 341 652355-99
info@sancona.com
www.sancona.com

// Registry Court: Leipzig HRB 32946
VAT Reg No.: DE308741810
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